Low-power dual 2-input AND gate Rev. 5 — 1 December 2011

Product data sheet

#### **General description** 1.

The 74AUP2G08 provides the dual 2-input AND function.

Schmitt-trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire  $V_{CC}$  range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire  $V_{CC}$  range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using IOFF. The IOFF circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

#### 2. **Features and benefits**

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
  - JESD8-12 (0.8 V to 1.3 V)
  - JESD8-11 (0.9 V to 1.65 V)
  - JESD8-7 (1.2 V to 1.95 V)
  - JESD8-5 (1.8 V to 2.7 V)
  - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
  - HBM JESD22-A114F Class 3A exceeds 5000 V
  - MM JESD22-A115-A exceeds 200 V
  - CDM JESD22-C101E exceeds 1 000 V
- Low static power consumption;  $I_{CC} = 0.9 \mu A$  (maximum)
- Latch-up performance exceeds 100 mA per JESD78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V<sub>CC</sub>
- I<sub>OFF</sub> circuitry provides partial power-down mode operation
- Multiple package options
- Specified from –40 °C to +85 °C and –40 °C to +125 °C



Low-power dual 2-input AND gate

## 3. Ordering information

g information				
Package				
Temperature range	Name	Description	Version	
–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1	
–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 $\times$ 1.95 $\times$ 0.5 mm	SOT833-1	
–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.35 \times 1 \times 0.5$ mm	SOT1089	
–40 °C to +125 °C	XSON8U	plastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body $3 \times 2 \times 0.5$ mm	SOT996-2	
–40 °C to +125 °C	XQFN8U	plastic extremely thin quad flat package; no leads; 8 terminals; UTLP based; body $1.6 \times 1.6 \times 0.5$ mm	SOT902-1	
–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.2 \times 1.0 \times 0.35$ mm	SOT1116	
–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 $\times$ 1.0 $\times$ 0.35 mm	SOT1203	
	Package         Temperature range         -40 °C to +125 °C         -40 °C to +125 °C	Package           Temperature range         Name           -40 °C to +125 °C         VSSOP8           -40 °C to +125 °C         XSON8           -40 °C to +125 °C         XSON8           -40 °C to +125 °C         XSON8U           -40 °C to +125 °C         XSON8U           -40 °C to +125 °C         XSON8U           -40 °C to +125 °C         XSON8U	PackageTemperature rangeNameDescription-40 °C to +125 °CVSSOP8plastic very thin shrink small outline package; 8 leads; body width 2.3 mm-40 °C to +125 °CXSON8plastic extremely thin small outline package; no leads; 8 terminals; body 1 × 1.95 × 0.5 mm-40 °C to +125 °CXSON8extremely thin small outline package; no leads; 8 terminals; body 1 × 1.95 × 0.5 mm-40 °C to +125 °CXSON8plastic extremely thin small outline package; no leads; 8 terminals; body 1.35 × 1 × 0.5 mm-40 °C to +125 °CXSON8Uplastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body 3 × 2 × 0.5 mm-40 °C to +125 °CXQFN8Uplastic extremely thin quad flat package; no leads; 8 terminals; UTLP based; body 1.6 × 1.6 × 0.5 mm-40 °C to +125 °CXSON8extremely thin small outline package; no leads; 8 terminals; UTLP based; body 1.6 × 1.6 × 0.5 mm-40 °C to +125 °CXSON8extremely thin small outline package; no leads; 8 terminals; UTLP based; body 1.6 × 1.6 × 0.5 mm-40 °C to +125 °CXSON8extremely thin small outline package; no leads; 8 terminals; body 1.2 × 1.0 × 0.35 mm-40 °C to +125 °CXSON8extremely thin small outline package; no leads; 8 terminals; body 1.2 × 1.0 × 0.35 mm	

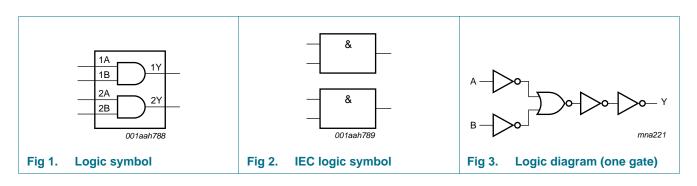
## 4. Marking

#### Table 2.Marking codes

5	
Type number	Marking code <sup>[1]</sup>
74AUP2G08DC	p08
74AUP2G08GT	p08
74AUP2G08GF	pE
74AUP2G08GD	p08
74AUP2G08GM	p08
74AUP2G08GN	pE
74AUP2G08GS	pE

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

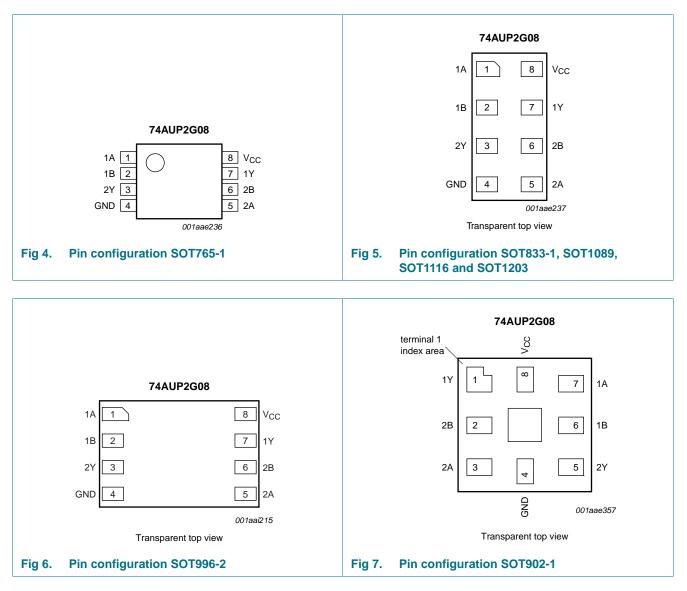
## 5. Functional diagram



Low-power dual 2-input AND gate

### 6. Pinning information

### 6.1 Pinning



### 6.2 Pin description

Symbol	Pin	Pin		
	SOT765-1, SOT833-1, SOT1089, SOT996-2, SOT1116 and SOT1203	SOT902-1		
1A, 2A	1, 5	7, 3	data input	
1B, 2B	2, 6	6, 2	data input	
GND	4	4	ground (0 V)	
1Y, 2Y	7, 3	1, 5	data output	
V <sub>CC</sub>	8	8	supply voltage	
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### 7. Functional description

#### Table 4.Function table<sup>[1]</sup>

Input	Output	
nA	nB	nY
L	L	L
L	Н	L
Н	L	L
Н	Н	Н

[1] H = HIGH voltage level;

L = LOW voltage level.

### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+4.6	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
Ι <sub>ΟΚ</sub>	output clamping current	V <sub>O</sub> < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode	<u>[1]</u> –0.5	+4.6	V
Ι <sub>Ο</sub>	output current	$V_{O} = 0 V \text{ to } V_{CC}$	-	±20	mA
I <sub>CC</sub>	supply current		-	+50	mA
I <sub>GND</sub>	ground current		-50	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to \ +125 \ ^{\circ}C$	[2] _	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For VSSOP8 packages: above 110 °C the value of P<sub>tot</sub> derates linearly at 8.0 mW/K. For XSON8, XSON8U and XQFN8U packages: above 118 °C the value of P<sub>tot</sub> derates linearly with 7.8 mW/K.

## 9. Recommended operating conditions

Table 6.	Operating conditions				
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	0	V <sub>CC</sub>	V
		Power-down mode; $V_{CC} = 0 V$	0	3.6	V
T <sub>amb</sub>	ambient temperature		-40	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 0.8 V \text{ to } 3.6 V$	-	200	ns/V

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## **10. Static characteristics**

#### Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T <sub>amb</sub> = 2	5 °C					
VIH	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.70\times V_{CC}$	-	-	V
		$V_{CC} = 0.9 V$ to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		$V_{CC}$ = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	-	V
V <sub>IL</sub>	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.30 \times V_{\text{CC}}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		$V_{CC}$ = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
V <sub>он</sub>	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O}$ = –20 $\mu A;$ V_{CC} = 0.8 V to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_0 = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.75\times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.11	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.32	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	2.05	-	-	V
		$I_0 = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_0 = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.72	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.6	-	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O}$ = 20 $\mu A;$ $V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	$0.3\times V_{CC}$	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.31	V
		$I_0 = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.31	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
l	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.1	μΑ
OFF	power-off leakage current	$V_{I}$ or $V_{O}$ = 0 V to 3.6 V; $V_{CC}$ = 0 V	-	-	±0.2	μΑ
$\Delta I_{OFF}$	additional power-off leakage current	$V_1$ or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.2	μΑ
lcc	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC};  I_{O} = 0 \; A; \\ V_{CC} = 0.8 \; V \; to \; 3.6 \; V \end{array}$	-	-	0.5	μΑ
∆l <sub>CC</sub>	additional supply current		<u>[1]</u> -	-	40	μΑ
Cı	input capacitance	$V_{CC}$ = 0 V to 3.6 V; $V_{I}$ = GND or $V_{CC}$	-	0.6	-	pF
Co	output capacitance	$V_{O} = GND; V_{CC} = 0 V$	-	1.3	-	pF

Low-power dual 2-input AND gate

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T <sub>amb</sub> = –	40 °C to +85 °C					
VIH	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.70\times V_{CC}$	-	-	V
		$V_{CC} = 0.9 V$ to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		$V_{CC}$ = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC}$ = 3.0 V to 3.6 V	2.0	-	-	V
V <sub>IL</sub>	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.30\times V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		$V_{CC}$ = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
V <sub>он</sub>	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O}$ = –20 $\mu\text{A};V_{CC}$ = 0.8 V to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.7\times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.03	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.30	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.97	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.85	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.67	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.55	-	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O}$ = 20 $\mu\text{A};V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		$I_0 = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.3\times V_{CC}$	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.37	V
		$I_0 = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.35	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.33	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.45	V
I	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.5	μΑ
OFF	power-off leakage current	$V_{I}$ or $V_{O}$ = 0 V to 3.6 V; $V_{CC}$ = 0 V	-	-	±0.5	μΑ
\l <sub>OFF</sub>	additional power-off leakage current	$V_1$ or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.6	μΑ
СС	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC};  I_{O} = 0 \; A; \\ V_{CC} = 0.8 \; V \; to \; 3.6 \; V \end{array}$	-	-	0.9	μΑ
∆I <sub>CC</sub>	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	<u>[1]</u> -	-	50	μΑ

### Table 7. Static characteristics ...continued

Low-power dual 2-input AND gate

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T <sub>amb</sub> = -	40 °C to +125 °C					
V <sub>IH</sub>	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.75\times V_{CC}$	-	-	V
		$V_{CC} = 0.9 V$ to 1.95 V	$0.70\times V_{CC}$	-	-	V
		$V_{CC}$ = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC}$ = 3.0 V to 3.6 V	2.0	-	-	V
V <sub>IL</sub>	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.25\times V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.30 \times V_{CC}$	V
		$V_{CC}$ = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC}$ = 3.0 V to 3.6 V	-	-	0.9	V
V <sub>он</sub>	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O}$ = –20 $\mu A;  V_{CC}$ = 0.8 V to 3.6 V	$V_{CC}-0.11$	-	-	V
		$I_0 = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.6\times V_{CC}$	-	-	V
		$I_0 = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	0.93	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.17	-	-	V
		$I_{O}$ = -2.3 mA; $V_{CC}$ = 2.3 V	1.77	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.67	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.40	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.30	-	-	V
/ <sub>OL</sub>	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O}$ = 20 $\mu A; V_{CC}$ = 0.8 V to 3.6 V	-	-	0.11	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	$0.33 \times V_{CC}$	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.41	V
		$I_0 = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.39	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.36	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.50	V
I	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.75	μA
OFF	power-off leakage current	$V_{I}$ or $V_{O}$ = 0 V to 3.6 V; $V_{CC}$ = 0 V	-	-	±0.75	μA
\I <sub>OFF</sub>	additional power-off leakage current	$V_1$ or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.75	μΑ
сс	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC};  I_{O} = 0 \; A; \\ V_{CC} = 0.8 \; V \; to \; 3.6 \; V \end{array}$	-	-	1.4	μΑ
∆l <sub>CC</sub>	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	<u>[1]</u> -	-	75	μA

#### Table 7. Static characteristics ... continued

[1] One input at  $V_{CC}$  – 0.6 V, other input at  $V_{CC}$  or GND.

## 11. Dynamic characteristics

#### **Dynamic characteristics** Table 8.

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol Parameter		Conditions		Tai	<sub>mb</sub> = 25 °	T <sub>amb</sub> = 25 °C		T <sub>amb</sub> = -40 °C to +125 °C		
				Min	Typ <mark>[1]</mark>	Max	Min	Max (85 °C)	Max (125 °C)	
C <sub>L</sub> = 5 p	F				1			1		
pd	propagation delay	nA or nB to nY; see Figure 8	[2]							
		$V_{CC} = 0.8 V$		-	17.0	-	-	-	-	ns
		$V_{CC}$ = 1.1 V to 1.3 V		2.6	5.1	10.8	2.1	11.7	12.9	ns
		$V_{CC}$ = 1.4 V to 1.6 V		1.6	3.7	6.5	1.5	7.5	8.3	ns
		$V_{CC}$ = 1.65 V to 1.95 V		1.3	3.0	5.2	1.3	6.1	6.7	ns
		$V_{CC}$ = 2.3 V to 2.7 V		1.1	2.4	4.0	1.0	4.8	5.3	ns
		$V_{CC}$ = 3.0 V to 3.6 V		1.0	2.2	3.5	0.9	4.3	4.8	ns
C <sub>L</sub> = 10	pF									
pd	propagation delay	nA or nB to nY; see Figure 8	[2]							
		$V_{CC} = 0.8 V$		-	20.6	-	-	-	-	ns
		$V_{CC}$ = 1.1 V to 1.3 V		2.4	6.0	12.5	2.2	13.6	15.0	ns
		$V_{CC}$ = 1.4 V to 1.6 V		2.0	4.3	7.6	1.8	8.9	9.8	ns
		$V_{CC}$ = 1.65 V to 1.95 V		1.7	3.6	6.1	1.6	7.2	7.9	ns
		$V_{CC}$ = 2.3 V to 2.7 V		1.4	2.9	4.8	1.3	5.7	6.3	ns
		$V_{CC}$ = 3.0 V to 3.6 V		1.3	2.7	4.2	1.2	4.7	5.2	ns
C <sub>L</sub> = 15	pF									
pd	propagation delay	nA or nB to nY; see Figure 8	[2]							
		$V_{CC} = 0.8 V$		-	24.1	-	-	-	-	ns
		$V_{CC}$ = 1.1 V to 1.3 V		3.4	6.8	14.2	3.1	15.7	17.3	ns
		$V_{CC}$ = 1.4 V to 1.6 V		2.3	4.9	8.6	2.1	10.1	11.2	ns
		$V_{CC}$ = 1.65 V to 1.95 V		1.9	4.0	6.9	1.8	8.2	9.0	ns
		$V_{CC}$ = 2.3 V to 2.7 V		1.7	3.4	5.5	1.6	6.5	7.2	ns
		$V_{CC}$ = 3.0 V to 3.6 V		1.5	3.1	4.8	1.5	5.9	6.5	ns
C <sub>L</sub> = 30	pF									
pd	propagation delay	nA or nB to nY; see Figure 8	[2]							
		$V_{CC} = 0.8 V$		-	34.4	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		4.6	9.1	19.4	4.1	21.8	24.0	ns
		$V_{CC}$ = 1.4 V to 1.6 V		3.4	6.4	11.5	2.9	13.6	15.0	ns
		$V_{CC}$ = 1.65 V to 1.95 V		2.6	5.3	9.1	2.4	10.9	12.1	ns
		$V_{CC}$ = 2.3 V to 2.7 V		2.3	4.5	7.2	2.2	8.6	9.5	ns

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Symbol	Parameter	Conditions	Ta	T <sub>amb</sub> = 25 °C			= –40 °C to	o +125 ℃	Unit
			Min	Typ <mark>[1]</mark>	Max	Min	Max (85 °C)	Max (125 °C)	
C <sub>L</sub> = 5 p	F, 10 pF, 15 pF and	30 pF							
C <sub>PD</sub>	power dissipation	$f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{\text{CC}}$ [3]							
	capacitance	$V_{CC} = 0.8 V$	-	2.5	-	-	-	-	pF
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	-	2.6	-	-	-	-	pF
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$	-	2.7	-	-	-	-	pF
		$V_{CC} = 1.65 \text{ V} \text{ to } 1.95 \text{ V}$	-	2.8	-	-	-	-	pF
		$V_{CC}$ = 2.3 V to 2.7 V	-	3.2	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	-	3.7	-	-	-	-	pF

#### Table 8. Dynamic characteristics ... continued

[1] All typical values are measured at nominal V<sub>CC</sub>.

#### [2] $t_{pd}$ is the same as $t_{PLH}$ and $t_{PHL}$ .

[3]  $C_{PD}$  is used to determine the dynamic power dissipation (P<sub>D</sub> in  $\mu$ W).

 $\label{eq:PD} \mathsf{P}_{\mathsf{D}} = C_{\mathsf{PD}} \times \mathsf{V}_{\mathsf{CC}}{}^2 \times f_i \times \mathsf{N} + \Sigma(C_\mathsf{L} \times \mathsf{V}_{\mathsf{CC}}{}^2 \times f_o) \text{ where:}$ 

 $f_i$  = input frequency in MHz;

 $f_o = output frequency in MHz;$ 

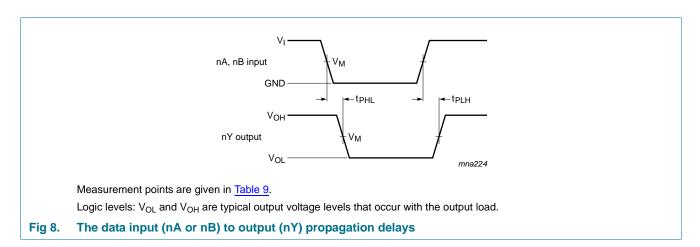
 $C_L$  = output load capacitance in pF;

V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$  = sum of the outputs.

### 12. Waveforms

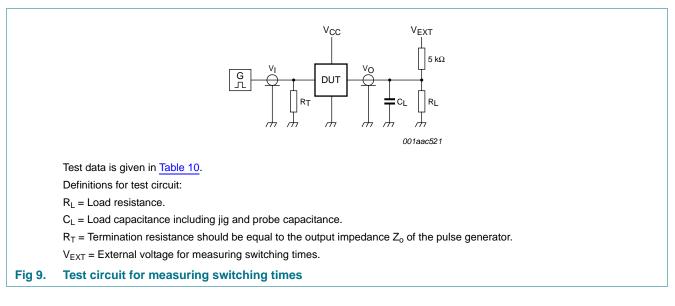


#### Table 9. **Measurement points**

Supply voltage	Output	Input				
V <sub>cc</sub>	V <sub>M</sub>	V <sub>M</sub>	VI	$t_r = t_f$		
0.8 V to 3.6 V	$0.5  imes V_{CC}$	$0.5  imes V_{CC}$	V <sub>CC</sub>	$\leq$ 3.0 ns		

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#### Table 10. Test data

Supply voltage	Load		V <sub>EXT</sub>		
V <sub>cc</sub>	CL	R <sub>L</sub> [1]	t <sub>PLH</sub> , t <sub>PHL</sub>	t <sub>PZH</sub> , t <sub>PHZ</sub>	t <sub>PZL</sub> , t <sub>PLZ</sub>
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k $\Omega$ or 1 M $\Omega$	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times,  $R_L = 5 k\Omega$ .

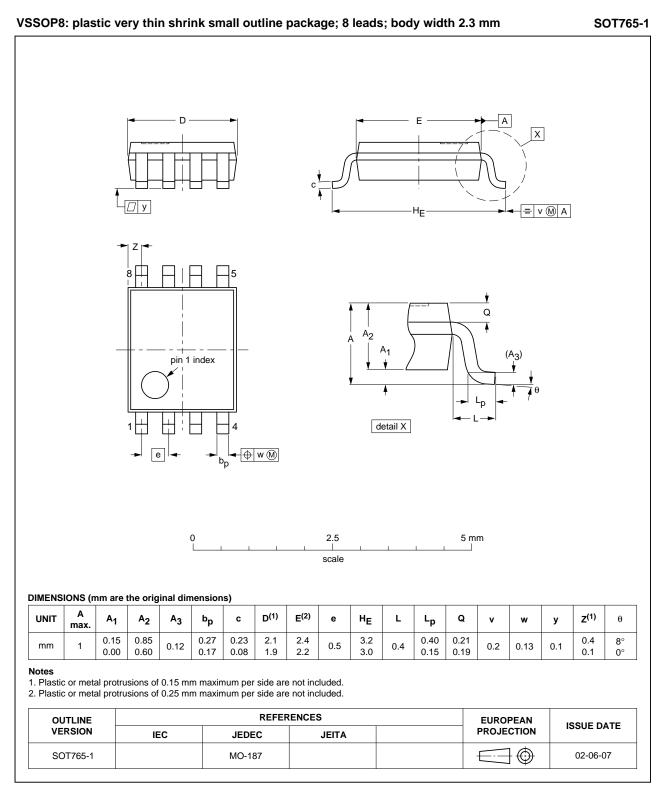
For measuring propagation delays, set-up and hold times and pulse width,  $R_L = 1 M\Omega$ .

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### 13. Package outline



#### Fig 10. Package outline SOT765-1 (VSSOP8)

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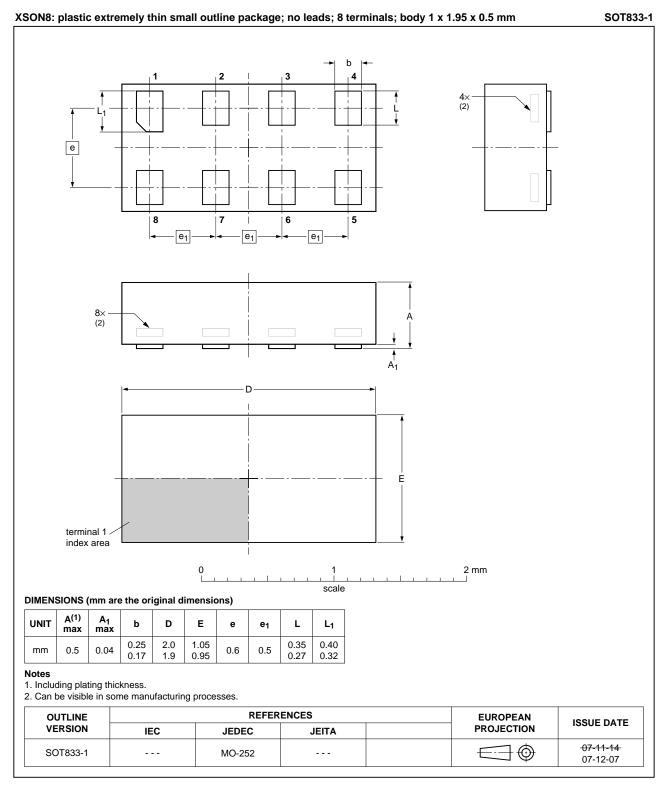
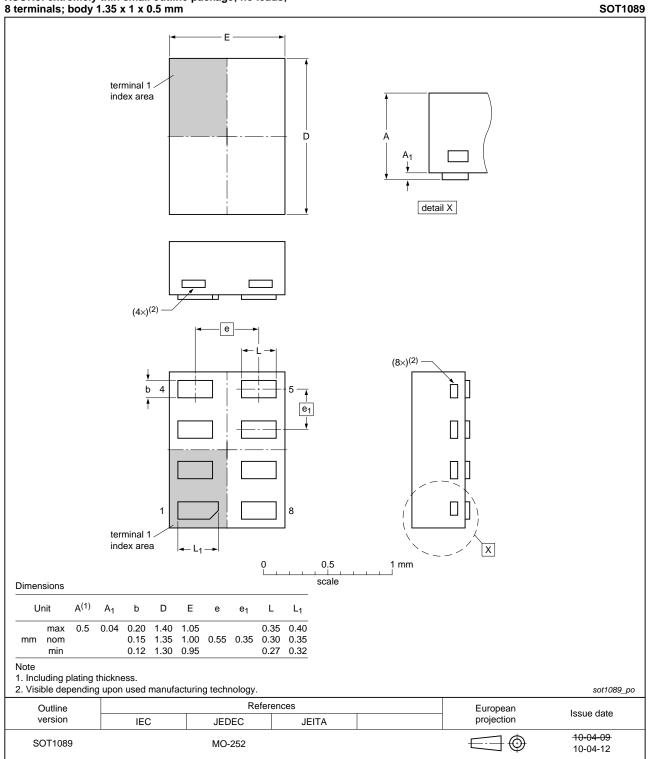


Fig 11. Package outline SOT833-1 (XSON8)

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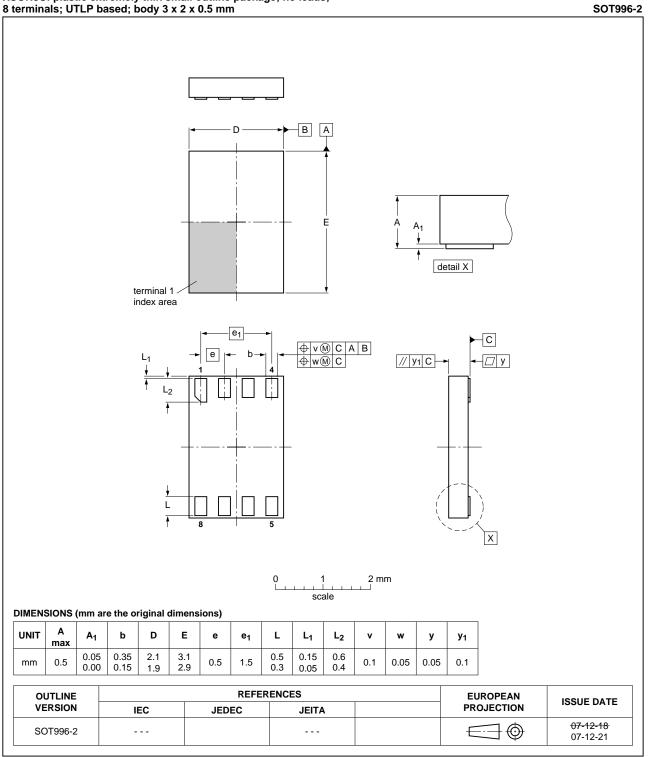
XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.35 x 1 x 0.5 mm

Fig 12. Package outline SOT1089 (XSON8)

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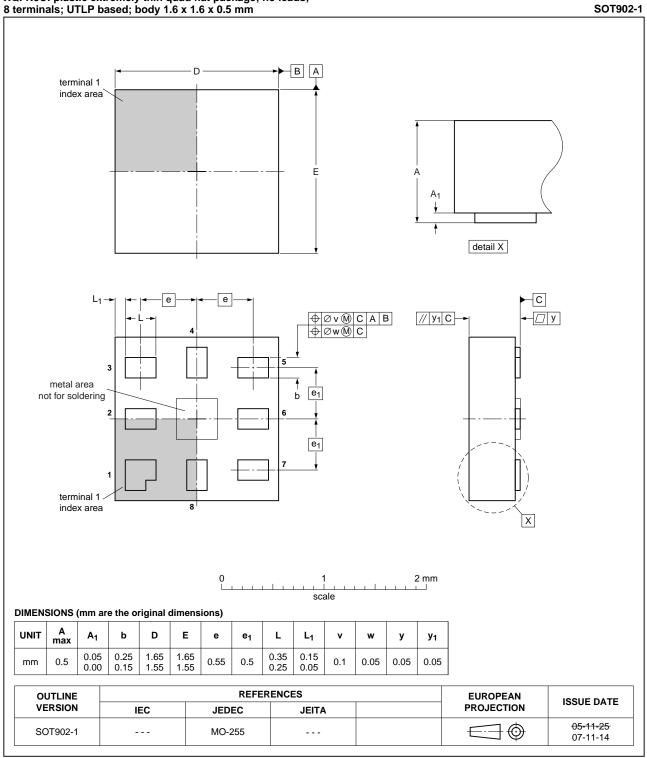


XSON8U: plastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body 3 x 2 x 0.5 mm

#### Fig 13. Package outline SOT996-2 (XSON8U)

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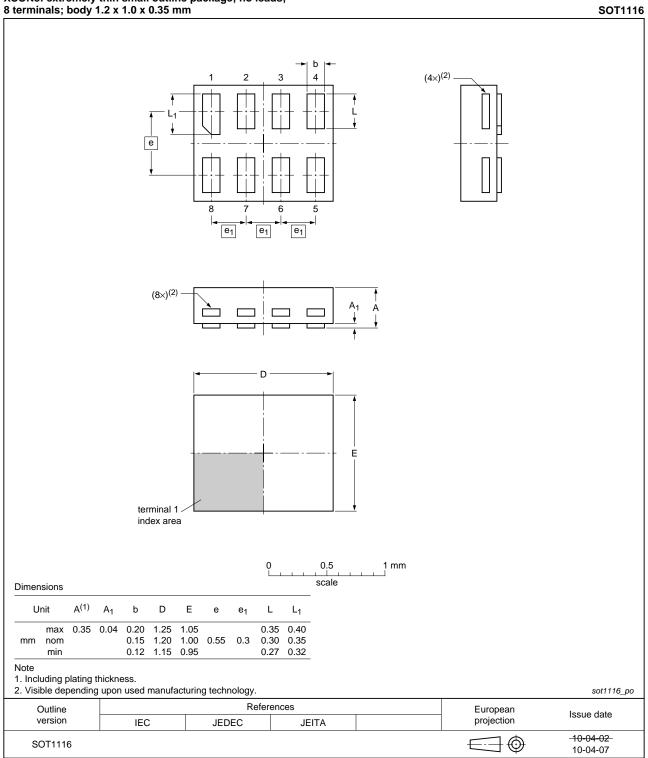


# XQFN8U: plastic extremely thin quad flat package; no leads; 8 terminals; UTLP based; body 1.6 x 1.6 x 0.5 mm

Fig 14. Package outline SOT902-1 (XQFN8U)

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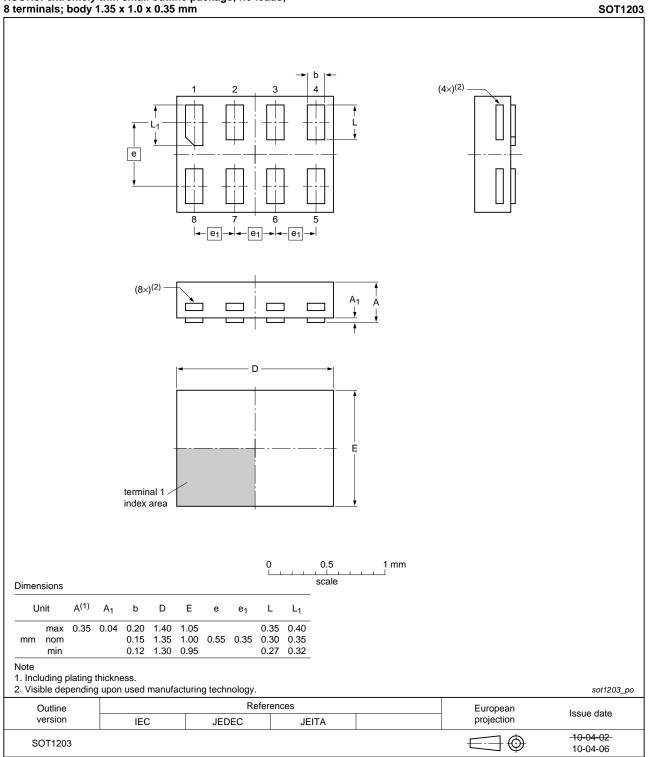
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# XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.2 x 1.0 x 0.35 mm

Fig 15. Package outline SOT1116 (XSON8)

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# XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.35 x 1.0 x 0.35 mm

Fig 16. Package outline SOT1203 (XSON8)

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### 14. Abbreviations

Table 11. Abbreviations		
Acronym	Description	
CDM	Charged Device Model	
DUT	Device Under Test	
ESD	ElectroStatic Discharge	
HBM	Human Body Model	
MM	Machine Model	

### **15. Revision history**

#### Table 12. Revision history **Document ID Release date** Data sheet status **Change notice** Supersedes 74AUP2G08 v.5 20111201 Product data sheet 74AUP2G08 v.4 -Modifications: • Legal pages updated. 74AUP2G08 v.4 20101109 Product data sheet 74AUP2G08 v.3 -74AUP2G08 v.3 20080529 Product data sheet 74AUP2G08 v.2 -74AUP2G08 v.2 20080407 Product data sheet 74AUP2G08 v.1 -74AUP2G08 v.1 20061006 Product data sheet --

### 16. Legal information

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Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Date of release: 1 December 2011 Document identifier: 74AUP2G08